

FORM PTO-1449 (MODIFIED)

LIST OF PATENTS AND  
PUBLICATIONS  
FOR APPLICANTS INFORMATION  
DISCLOSURE STATEMENTATTORNEY DOCKET NO.  
SP01-302

SERIAL NO.

10/035659

APPLICANT Karl Heinz Buchanan, et al.

FILING DATE  
October 26, 2001

GROUP: 1731

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date if Approp.
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub- Class	Translation Yes No
	AL						
	AM						
	AN						
	AO						
	AP						
	AQ						

## OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

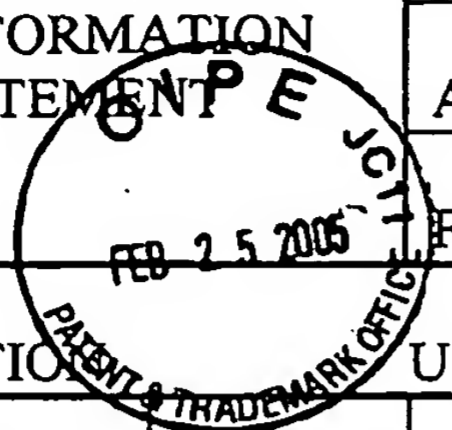
AR	W.P. Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review" J. Electrochemical Society, Inc., Vol. 138, No.1, January 1991
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DATE CONSIDERED:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (MODIFIED)	ATTORNEY DOCKET NO. SP01-302	SERIAL NO. 10/035659
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANTS INFORMATION DISCLOSURE STATEMENT	APPLICANT: COOK, et al.	
	FILING DATE 10/26/2001	GROUP: 1731



REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date if Approp.
	AA	4,186,999	2/5/80	Harwood et al	350	96.21	
	AB	4,530,452	7/23/85	Balyasny et al	225	96	
	AC	4,626,068	12/2/86	Caldwell	350	96.34	
	AD	5,183,710	2/2/93	Gerbino	428	405	
	AE	5,346,583	9/13/94	Basavanhally	156	629	
	AF	5,451,547	9/19/95	Himi et al	437	225	
	AG	5,452,122	9/19/95	Tsuneda et al	359	281	
	AH	5,579,421	11/26/96	Duvall et al	385	14	
	AI	5,631,986	5/20/97	Frey et al	385	78	
	AJ	5,846,638	12/8/98	Meissner	428	220	
	AK	5,852,622	12/22/98	Meissner et al	372	39	
	AL	5,989,372	11/23/99	Momoda et al	156	89.11	
	AM	6,030,883	2/29/00	Nishimoto et al	438	455	
	AN	6,048,103	4/11/00	Furukata et al	385	73	
	AO	6,249,619	6/19/01	Bergmann et al	385	11	
	AP	6,275,336	8/14/01	Yoshikawa et al	359	484	
	AQ	6,359,733	3/19/02	Iwatsuka et al	359	500	
	AR	6,583,029	6/24/03	Abe et al	438	455	
	AS	2002/0108556	8/15/02	Ebbers	117	2	
	AT	2003/0079503	5/1/03	Cook et al	65	407	
	AU	2003/0079823	5/1/03	Sabia	156	99	
	AV	2003/0081906	5/1/03	Filhaber et al	385	60	
	AW	2003/0206345	11/6/03	Sabia et al	359	484	
	AX	2003/0206347	11/6/03	Sabia et al	359	484	
	AY	2003/0081930	5/1/03	Filhaber et al	385	147	
	AZ	4,960,331	10/2/90	Goldman et al	356	350	
	BA	5,319,483	6/7/94	Krasinski et al	359	113	
	BB	5,441,803	8/15/95	Meissner	428	220	
	BC	5,689,519	11/18/97	Fermann et al	372	18	
	BD	6,120,917	9/19/00	Eda	428	692	
	BE	6,548,176	4/15/03	Gwo	428	420	
	BF	6,621,630	9/16/03	Iwatsuka	359	484	
	BG	5,915,193	6/22/99	Tong et al.	438	455	
	BH	5,785,874	7/28/98	Eda	216	24	
	BI	5,932,048	8/3/99	Furukawa et al.	156	153	
	BJ	6,129,854	10/10/00	Ramsey et al.	216	18	
	BK	6,153,495	11/28/00	Kub et al.	438	459	
	BL	6,178,779	1/30/01	Drouart et al.	65	391	

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BM	6,098,429	8/8/01	Mazabraud et al.	65	392	
BP	4,407,667	10/4/83	LeNoane et al.	65	3.11	

# FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Sub-Class	Translation	
						Yes	No
BO	WO01/98225	12/27/01	PCT	C03C	27/06		
BP	WO00/17698	3/30/00	PCT	G02F	1/09		
BQ	DE19731075	1/21/99	Germany (English Abstract)	C03C	29/00		
BR	DE2130905	1/11/73	Germany (English Abstract)	H01J	19/56		
BS	08-146351	6/7/96	Japan (English Abstract)	G02B	27/28		
BT	2002321947	4/25/01	Japan (English Abstract)	C03C	27/00		
BU	03-115178	5/16/91	Japan (English Abstract)	C04B	37/00		
BV	52-78450	7/1/77	Japan (English Abstract)	C03B	37/00		
BW	1 057 793A1	12/6/00	EPO	C03B	37/027	X	

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BX	ONISHI et al., "A novel temperature compensation method for SAW devices using direct bonding Techniques," <i>Ultrasonics Symp</i> , 1997, IEEE Proceedings, 5-8 Oct, 1997 Pages 227-230.
BY	Arthur Landrock; "Surface Preparation of Adherends"; Adhesives Technology Handbook; 1985; page 117-118
BZ	A. Sayah, D. Solignac, T. Cueni, M.A.M. Gijis, "Development of novel low temperature bonding technologies for microchip chemical analysis applications," <i>Sensors and Actuators</i> , 84 August (2000) pp. 103-108.
CA	P. Rangsten, O. Vallin, K. Hermansson, Y. Backlund, "Quartz-to-Quartz Direct Bonding," <i>Journal of the Electrochemical Society</i> , V. 146, N. 3, pp. 1104-1105, (1999).
CB	H. Nakanishi, T. Nishimoto, M. Kanai, T. Saitoh, R. Nakamura, T. Yoshida, S. Shoji, "Condition optimization, reliability evaluation of SiO <sub>2</sub> -SiO <sub>2</sub> HF bonding and its application for UV detection micro flow cell," <i>Sensors and Actuators</i> , V. 83, pp. 136-141, May 2000.
CC	A. Yamada, T. Kawasaki, M. Kawashima, "Bonding Silicon wafer to Silicon Nitride With Spin-on Glass as Adhesive," <i>Electronics Letters</i> , March 26, 1987, Vol. 23, No. 7 Pages 314-315.
CD	D.J. Harrison, Karl Fluri, Kurt Seiler, Zhonghui Fan, Carlo S. Effenhauser, Andreas Manz, "Micromachining a Miniaturized Capillary Electrophoresis-Based Chemical Analysis System on a Chip," <i>Science</i> , V. 261, August 13 (1993) 895-897.
CE	Dong-Woon Shin, Doo-Jin Choi, Geung-Ho Kim, "The Stacking Faults and Their Strain Effect at the Si/SiO <sub>2</sub> Interfaces of a Directly Bonded SOI (silicon on insulator)," <i>Thin Solid Films</i> , V. 346, pp. 169-173, 1999.
CF	Q-Y. Tong, T-H Lee, and U. Gosele, "The Role of Surface Chemistry in Bonding of Standard Silicon Wafers," <i>J. Electrochemical Society</i> V. 144, N. 1, pp. 384-389, January 1997
CG	

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